ELSEVIER

Contents lists available at ScienceDirect

## Journal of Alloys and Compounds

journal homepage: www.elsevier.com/locate/jallcom



# Bonding and hardness of LnMgAl<sub>11</sub>O<sub>19</sub>(Ln = La; Pr; Nd; Sm; Eu; Gd)

Zhiping Li, Faming Gao\*

Key Laboratory of Apllied Chemistry, Yanshan University, Qinhuangdao 066004, China

#### ARTICLE INFO

Article history: Received 12 May 2010 Received in revised form 31 August 2010 Accepted 1 September 2010 Available online 9 September 2010

Keywords: Bond Hardness LnMgAl<sub>11</sub>O<sub>19</sub>

#### ABSTRACT

The chemical bond parameters of  $LnMgAl_{11}O_{19}$  (Ln=La, Pr, Nd, Sm, Eu, Gd) were calculated using the chemical bond dielectric theory of complex structural crystals. The hardness of  $LnMgAl_{11}O_{19}$  was predicted. The results indicated that the origin of the high hardness of  $LnMgAl_{11}O_{19}$  results mainly from AlO units.

© 2010 Elsevier B.V. All rights reserved.

#### 1. Introduction

LaMgAl<sub>11</sub>O<sub>19</sub> has a slightly distorted magnetoplumbite (PbFe<sub>12</sub>O<sub>19</sub>) structure, belonging to the hexagonal space group P6<sub>3</sub>/mmc [1]. La<sup>3+</sup> can be substituted with a lanthanide ion Ln<sup>3+</sup> (where Ln = Pr, Nd, Sm, Eu, Gd). Lanthanum-magnesium hexaaluminate LaMgAl<sub>11</sub>O<sub>19</sub> is a remarkable good laser host for Nd<sup>3+</sup> ions (LNA). LnMgAl<sub>11</sub>O<sub>19</sub> can also be used as luminescence materials. saturable absorber Q-switches [2]. Oxides with magnetoplumbite structure of the general composition, LnMAl<sub>11</sub>O<sub>19</sub> (Ln=La to Gd), have high melting point, high thermal expansion, and low thermal conductivity which make them suitable for applications as high-temperature thermal barrier coatings [3]. The first growth of LaMgAl<sub>11</sub>O<sub>19</sub> crystal by using verneuil method (flame fusion method) and floating zone method was reported by Saber and Lejus [1]. For the various applications, LnMgAl<sub>11</sub>O<sub>19</sub> crystals should also possess the excellent mechanical properties. The hardness of LnMgAl<sub>11</sub>O<sub>19</sub> crystals are thus measured [1]. In this paper, we will employ the dielectric theory of complex structure crystals to calculate the chemical bond parameters of LnMgAl<sub>11</sub>O<sub>19</sub>, and apply the obtained chemical bond parameters to analyzed their hardness.

### 2. Theoretical method

A chemical bond theory of complex structure crystals is proposed by Zhang [4,5]. Its crucial step is decomposing the complex

crystal into pseudobinary crystals each containing only one type of chemical bond. For the multibond crystal  $A_a B_b \dots$ , the subformula for any kind of chemical bond A—B can be expressed as:

$$\left[\frac{N(B-A)a}{N_{CA}}\right]A\left[\frac{N(A-B)b}{N_{CB}}\right]B\tag{1}$$

where A, B, . . . represent different elements or different sites of the same element in the crystal formula, and  $a,b,\ldots$  represent numbers of the corresponding element, N(B-A) represents the number of B ions in the coordination group of A ion, and  $N_{CA}$  represents the nearest coordination number of A ion. These binary crystals are related to each other, and every binary crystal includes only one type of chemical bond. However, the properties of these psuedo-binary crystals are different from those of real binary crystals, although their chemical bond parameters can be calculated in a similar way. According to Eq. (1), each type of bond has its corresponding subformula, and the sum of all subformula equals the crystal formula, which is called the bond-valence equation.

On the analogy of the work of Phillips [6], the average energy gap  $E_g^{\mu}$  for every  $\mu$ bond in the psuedobinary crystals can be separated into homopolar  $E_h^{\mu}$  and heteropolar  $C^{\mu}$  parts. The homopolar gap  $E_h^{\mu}$  can be interpreted as produced by the symmetric part of the total potential, while the ionic or charge-transfer gap  $C^{\mu}$  results from the effect of the antisymmetric part. The average valence-conduction band gap is give by

$$(E_g^{\mu})^2 = (E_b^{\mu})^2 + (C^{\mu})^2$$
 (2)

The ionicity and covalency of any type of chemical bond is defined as follows

$$f_i^{\mu} = (C^{\mu})^2 / (E_g^{\mu})^2 \tag{3}$$

<sup>\*</sup> Corresponding author. Key Laboratory of Apllied Chemistry, Yanshan University, Qinhuangdao 066004, PR China. Tel.: +86 3358061569; fax: +86 3358061569. E-mail address: gfm0827@sina.com (F. Gao).

$$f_c^{\mu} = (E_b^{\mu})^2 / (E_g^{\mu})^2 \tag{4}$$

and

$$E_h^{\mu} = 39.74/(d^{\mu})^{2.48}(eV) \tag{5}$$

where  $d^{\mu}$  is the bond length. For any binary crystal, i.e.  $AB_n$  type compounds, the heteropolar  $C^{\mu}$  part is defined as

$$(6)C^{\mu} = 14.4b^{\mu}[(Z_{A}^{\mu})^{*} + \Delta Z_{A}^{\mu} - n(Z_{B}^{\mu})^{*}]e^{-k_{s}^{\mu}r_{0}^{\mu}}/r_{0}^{\mu}(eV)$$

 $r_0^{\mu} = d^{\mu}/2$ 

$$k_{\rm s}^{\mu} = \left(4k_{\rm F}^{\mu}/\pi a_{\rm B}\right)^{1/2} = 1.551(k_{\rm F}^{\mu})^{1/2}$$
 (7)

$$(k_{\rm F}^{\mu})^3 = 3\pi^2 N_{\rm e}^{\mu} \tag{8}$$

$$N_{\rm e}^{\mu} = (n_{\rm e}^{\mu})^* / v_{\rm b}^{\mu} \tag{9}$$

$$(n_{\rm e}^{\mu})^* = [(Z_{\rm A}^{\mu})^*/N_{\rm CA}^{\mu} + (Z_{\rm R}^{\mu})^*/N_{\rm CB}^{\mu}] \tag{10}$$

$$v_{\rm b}^{\mu} = (d^{\mu})^3 / \sum_{\nu} [(d^{\nu})^3 N_{\rm b}^{\nu}] \tag{11}$$

where  $v_b{}^\mu$  is the bond volume,  $(n_e{}^\mu)^*$  is the number of effective valence electrons per  $\mu$  bond,  $N_e{}^\mu$  is the number of valence electrons of  $\mu$  bond per cubic centimeter.  $k_F{}^\mu$  and  $k_S{}^\mu$  are Fermi wave number and Thomas-Fermi screening wave number of valence electron in binary crystal composed of only one type of bond  $\mu$ , respectively.  $a_B$  is the Bohr radius and n is the ratio of element B to element A in the subformula.  $(Z_A{}^\mu)^*$  and  $(Z_B{}^\mu)^*$  are the number of effective valence electrons of the A and B ions, respectively, and  $(Z_A{}^\mu)^* = Q_{AB}^\mu \cdot N_{CA}^\mu, (Z_B{}^\mu)^* = [(Q_{AB}^\mu \cdot N_{CB}^\mu)/(8 - Z_B^\mu)] \cdot Z_B^\mu, Q_{AB}^\mu$  is Pauling bond valence of A—B bonds,  $Z_B{}^\mu$  is the number of valence electrons of the B atoms.  $\Delta Z_A{}^\mu$  is correction factor from d electron effects such as the crystal field stable energy and Janh-Teller effect, etc [7,8].  $b^\mu$  is proportional to the square of the average coordination number  $N_c{}^\mu$ 

$$b^{\mu} = \beta (N_c^{\mu})^2 \tag{12}$$

$$N_c^{\mu} = N_{CA}^{\mu}/(1+n) + nN_{CB}^{\mu}/(1+n) \tag{13}$$

The value of  $\beta$  can be deduced from the Kramers-Kronig relation of dielectric function at the long wave limit, which is written as

$$\chi^{\mu} = \left[ (4\pi N_{\rho}^{\mu} e^{2}/m) D^{\mu} / (E_{\sigma}^{\mu})^{2} \right] (1 - E_{\sigma}^{\mu} / 4E_{F}^{\mu} + (E_{\sigma}^{\mu})^{2} / 48(E_{F}^{\mu})^{2}) \quad (14)$$

$$\varepsilon(\infty) = 1 + \chi = 1 + \sum_{\mu} F^{\mu} \chi^{\mu} \tag{15}$$

where  $\chi$  is the macroscopic linear susceptibility,  $\chi^{\mu}$  is the total macroscopic susceptibility of a binary crystal composed of only one type of bond  $\mu$ ,  $E_F^{\mu}$  is Fermi energy,  $F^{\mu}$  is the fraction of the

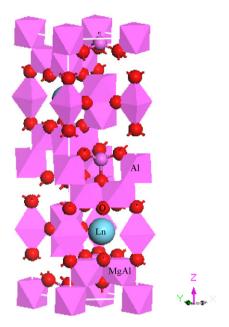


Fig. 1. Crystal structure of LnMgAl<sub>11</sub>O<sub>19</sub>.

binary crystal composing the actual complex crystal.  $D^\mu$  is periodic dependent constants.

#### 3. Results and discussions

LnMgAl $_{11}$ O $_{19}$  have a structural type close to the magneto-plumbite structure, PbFe $_{12}$ O $_{19}$ , in which Al $^{3+}$  is substitutes for Fe $^{3+}$  in the network, Ln $^{3+}$  takes the place of Pb $^{2+}$ , and Mg $^{2+}$  takes the place of one Fe $^{3+}$ . Al(3) and Mg inhabit the same site 4f $_1$ . The coordination number of Ln is 12, Al(1), Al(4), and Al(5) are all 6, Al(2) is 5, Al(3) and Mg is 4, O(1), O(2), and O(4) are 4, O(3) is 5. The crystal structure is shown in Fig. 1. According to Eq. (1), the bond-valence equation of LnMgAl $_{11}$ O $_{19}$  is expressed as:

$$\begin{split} &\text{LnMgAl}_{11}\text{O}_{19} = \text{LnAl}(1)\text{Al}(2)\text{MgAl}(3)\text{Al}(4)_{6}\text{Al}(5)_{2}\text{O}(1)_{2}\text{O}(2)_{2} \\ &\text{O}(3)_{3}\text{O}(4)_{6}\text{O}(5)_{6} = 1/2\text{LnO}(3)_{12/5} + 1/2\text{LnO}(5)_{3} + \text{Al}(1)\text{O}(4)_{3/2} \\ &+ 2/5\text{Al}(2)\text{O}(1)_{5/4} + 3/5\text{Al}(2)\text{O}(3) + 1/2[\text{Al}(3)_{1/2}\text{Mg}_{1/2}]\text{O}(2) \\ &+ 3/2[\text{Al}(3)_{1/2}\text{Mg}_{1/2}]\text{O}(4) + \text{Al}(4)\text{O}(1)_{3/2} + \text{Al}(4)\text{O}(2)_{3/2} \\ &+ 2\text{Al}(4)\text{O}(4)_{3/2} + 2\text{Al}(4)\text{O}(5)_{3/2} + \text{Al}(5)\text{O}(3)_{6/5} + \text{Al}(5)\text{O}(5)_{3/2} \quad (16) \end{split}$$

The Pauling bond valences of the bonds in LnMgAl<sub>11</sub>O<sub>19</sub> are shown in Fig. 2. Using the Pauling bond valences,  $(Z_A{}^\mu)^*$  and  $(Z_B{}^\mu)^*$  can be determined.

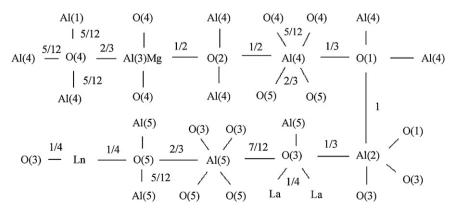


Fig. 2. Coordination and Pauling bond valences in LnMgAl<sub>11</sub>O<sub>19</sub>.

Table 1 Chemical bond parameters and hardness of LnMgAl11O<sub>19</sub>. where  $H^{\mu}_{\nu}$  is hardness of psuedobinary compound composed of  $\mu$ -type bond,  $H_{av}$  and  $H_{v}$  expt are calculated average value and experimental microhardness, respectively.  $Q^{\mu}_{AB}$  is Pauling bond valence of A—B bonds.

	Bond type	$Q_{AB}^{\mu}$	$d^{\mu}$ (Å)	$v_{\rm b}{}^{\mu}(\mathring{\mathbb{A}}^3)$	$N_{\rm e}^{\mu}$ (Å <sup>-3</sup> )	$E_{\rm h}^{\mu}$ (eV)	$E_g^{\mu}$ (eV)	$f_i^{\mu}$	$\chi^{\mu}$	$H_{v}^{\mu}$	H <sub>v av</sub> (GPa)	H <sub>v expt</sub> .(GPa) [2
aMgAl <sub>11</sub> O <sub>19</sub>	LaO3	1/4	2.810	9.244	0.108	3.065	21.306	0.979	0.202	1.912	15.5	16.2
	LaO5	1/4	2.676	7.983	0.125	3.460	17.398	0.960	0.425	2.434		
	Al104	1/2	1.881	2.773	0.721	8.294	19.887	0.826	2.114	21.997		
	Al2O1	1	2.191	4.382	0.913	5.681	14.432	0.845	5.435	17.235		
	Al2O3	1/3	1.867	2.711	0.492	8.449	15.484	0.702	2.376	20.117		
	Al3MgO2	1/2	1.870	2.724	0.734	8.415	11.945	0.504	6.410	33.154		
	Al3MgO4	2/3	1.839	2.591	1.029	8.771	13.622	0.585	6.974	39.271		
	Al403	7/12	1.974	3.205	0.728	7.358	24.072	0.907	1.405	17.843		
	Al405	5/12	1.867	2.711	0.615	8.449	18.505	0.792	2.068	20.988		
	Al5O1	1/3	1.87	2.724	0.489	8.415	16.593	0.743	2.031	19.031		
	Al5O2	1/2	1.951	3.094	0.646	7.575	18.304	0.829	2.241	18.617		
	Al504	5/12	1.973	3.200	0.521	7.367	16.343	0.797	2.252	16.287		
	Al505	2/3	1.841	2.599	1.026	8.748	24.102	0.868	2.063	27.903		
PrMgAl <sub>11</sub> O <sub>19</sub>	PrO3	1/4	2.794	9.087	0.110	3.109	21.590	0.979	0.200	1.962	15.6	15.6
	PrO5		2.679	8.010		3.450	17.353	0.960	0.426	2.422	13.0	13.0
	Al104	1/4 1/2	1.873	2.737	0.125 0.731	8.382	20.080	0.826	2.100	22.430		
	Al201		2.196	4.412	0.907	5.649	14.351	0.845	5.460	17.060		
	Al201 Al203	1										
		1/3	1.759	2.267	0.588	9.794	17.679	0.693	2.174	26.561		
	Al3MgO2	1/2	1.862	2.689	0.744	8.505	12.066	0.503	6.363	33.820		
	Al3MgO4	2/3	1.841	2.599	1.026	8.748	13.588	0.586	6.987	39.075		
	Al403	7/12	1.975	3.209	0.727	7.349	24.044	0.907	1.406	17.802		
	Al405	5/12	1.864	2.698	0.618	8.482	18.572	0.791	2.063	21.144		
	Al5O1	1/3	1.86	2.681	0.497	8.528	16.792	0.742	2.015	19.511		
	Al502	1/2	1.949	3.084	0.648	7.594	18.347	0.829	2.237	18.704		
	Al504	5/12	1.967	3.171	0.526	7.423	16.456	0.797	2.242	16.516		
	Al5O5	2/3	1.838	2.587	1.031	8.783	24.192	0.868	2.057	28.110		
NdMgAl <sub>11</sub> O <sub>19</sub>	NdO3	1/4	2.893	10.087	0.099	2.852	19.906	0.979	0.214	1.678	15.5	16.2
	NdO5	1/4	2.709	8.282	0.121	3.356	16.914	0.961	0.435	2.304		
	Al104	1/2	1.872	2.733	0.732	8.393	20.104	0.826	2.099	22.485		
	Al201	1	2.192	4.388	0.912	5.675	14.416	0.845	5.440	17.200		
	Al2O3	1/3	1.758	2.263	0.589	9.808	17.701	0.693	2.172	26.631		
	Al3MgO2	1/2	1.859	2.676	0.747	8.539	12.111	0.503	6.345	34.074		
	Al3MgO4	2/3	1.84	2.595	1.028	8.760	13.605	0.585	6.981	39.173		
	Al4O3	7/12	1.973	3.200	0.729	7.367	24.100	0.907	1.403	17.884		
	Al4O5	5/12	1.862	2.689	0.620	8.505	18.617	0.791	2.060	21.249		
	Al5O1	1/3	1.859	2.676	0.498	8.539	16.812	0.742	2.014	19.559		
	Al5O2	1/2	1.947	3.075	0.650	7.614	18.390	0.829	2.233	18.792		
	Al504	5/12	1.965	3.161	0.527	7.442	16.494	0.796	2.238	16.593		
	Al505	2/3	1.836	2.578	1.034	8.807	24.252	0.868	2.054	28.249		
SmMgAl <sub>11</sub> O <sub>19</sub>	SmO3	1/4	2.791	9.057	0.110	3.117	21.644	0.979	0.200	1.971	15.8	16.4
Sillivign:11O19	SmO5	1/4	2.671	7.939	0.126	3.476	17.473	0.960	0.424	2.455	15.0	10.4
	Al104		1.870	2.724	0.734	8.415	20.152	0.826	2.095	22.595		
		1/2										
	Al201	1	2.196	4.412	0.907	5.649	14.351	0.845	5.460	17.060		
	Al203	1/3	1.757	2.260	0.590	9.822	17.724	0.693	2.170	26.702		
	Al3MgO2	1/2	1.855	2.659	0.752	8.585	12.173	0.503	6.322	34.416		
	Al3MgO4	2/3	1.839	2.591	1.029	8.771	13.622	0.585	6.974	39.271		
	Al403	7/12	1.971	3.190	0.731	7.386	24.156	0.907	1.401	17.966		
	Al405	5/12	1.861	2.685	0.621	8.516	18.639	0.791	2.058	21.301		
	Al5O1	1/3	1.857	2.668	0.500	8.562	16.852	0.742	2.010	19.657		
	Al502	1/2	1.945	3.065	0.652	7.633	18.433	0.829	2.230	18.880		
	Al504	5/12	1.963	3.151	0.529	7.461	16.532	0.796	2.234	16.671		
	A15O5	2/3	1.835	2.574	1.036	8.819	24.282	0.868	2.052	28.319		
EuMgAl <sub>11</sub> O <sub>19</sub>	EuO3	1/4	2.791	9.057	0.110	3.117	21.644	0.979	0.200	1.971	15.7	
	EuO5	1/4	2.676	7.983	0.125	3.460	17.398	0.960	0.425	2.434		
	Al104	1/2	1.871	2.729	0.733	8.404	20.128	0.826	2.097	22.540		
	Al201	1	2.193	4.394	0.910	5.668	14.399	0.845	5.445	17.165		
	Al2O3	1/3	1.757	2.260	0.590	9.822	17.724	0.693	2.170	26.702		
	Al3MgO2	1/2	1.860	2.681	0.746	8.528	12.096	0.503	6.351	33.989		
	Al3MgO4	2/3	1.839	2.591	1.029	8.771	13.622	0.585	6.974	39.271		
	Al403	7/12	1.973	3.200	0.729	7.367	24.100	0.907	1.403	17.884		
	Al4O5	5/12	1.861	2.685	0.621	8.516	18.639	0.791	2.058	21.301		
	Al5O1	1/3	1.858	2.672	0.499	8.551	16.832	0.742	2.012	19.608		
	Al5O2	1/2	1.947	3.075	0.650	7.614	18.390	0.829	2.233	18.792		
	Al504	5/12	1.965	3.161	0.527	7.442	16.494	0.796	2.238	16.593		
	Al505	2/3	1.836			8.807		0.868	2.054	28.249		
				2.578	1.034		24.252				15.0	
GdMgAl <sub>11</sub> O <sub>19</sub>	GdO3	1/4	2.789	9.038	0.111	3.123	21.680	0.979	0.199	1.978	15.9	
	GdO5	1/4	2.668	7.912	0.126	3.486	17.518	0.960	0.423	2.467		
	Al104	1/2	1.867	2.711	0.738	8.449	20.226	0.826	2.090	22.761		
	Al2O1	1	2.184	4.340	0.922	5.726	14.546	0.845	5.400	17.485		
	Al2O3	1/3	1.756	2.256	0.591	9.836	17.746	0.693	2.169	26.774		
	Al3MgO2	1/2	1.852	2.646	0.756	8.619	12.219	0.502	6.304	34.676		
	Al3MgO4	2/3	1.837	2.583	1.033	8.795	13.657	0.585	6.961	39.468		
	Al403	7/12	1.968	3.175	0.735	7.414	24.241	0.906	1.398	18.090		
	Al405	5/12	1.859	2.676	0.623	8.539	18.684	0.791	2.055	21.407		
			1.855	2.659	0.501	8.585	16.893	0.742	2.007	19,756		
	Al5O1	1/3	1.855 1.943	2.659 3.056	0.501 0.654	8.585 7.653	16.893 18.477	0.742 0.828	2.007 2.226	19.756 18.969		
			1.855 1.943 1.961	2.659 3.056 3.142	0.501 0.654 0.531	8.585 7.653 7.480	16.893 18.477 16.570	0.742 0.828 0.796	2.007 2.226 2.231	19.756 18.969 16.749		

The dielectric constant of the LaMgAl<sub>11</sub>O<sub>19</sub> is known [1]. By using the Zhang's theory, the calculated value of  $\beta$  of the LaMgAl<sub>11</sub>O<sub>19</sub> is 0.097. The chemical bond parameters for each type of constituent chemical bonds of LnMgAl<sub>11</sub>O<sub>19</sub> are listed in Table 1.

We may study the hardness of LnMgAl<sub>11</sub>O<sub>19</sub> crystals by using the obtained chemical bond parameters. The average hardness  $H_{\nu}$  of complex crystals may be calculated by a geometric average of hardness of psuedobinary compound composed of  $\mu$ -type bond as follow [9]:

$$H_{\nu} = \left[ \prod_{\nu}^{\mu} (H_{\nu}^{\mu})^{n^{\mu}} \right]^{1/\Sigma n^{\mu}} \tag{17}$$

$$H_{\nu}^{\mu} = 350(N_{e}^{\mu})^{2/3} e^{-1.191 f_{i}^{\mu}} / (d^{\mu})^{2.5}$$
(18)

where  $n^\mu$  is the number of bond of type  $\mu$  composing the actual complex crystal. Results are listed in Table 1

From Table 1, it is seen that the hardness of pseudobinary crystals composed of LnO bonds is far lower than that of crystals composed of AlO bonds. Namely, the origin of the high hardness of LnMgAl<sub>11</sub>O<sub>19</sub> results mainly from AlO units. According to Eq. (11), bond density or electronic density, bond length, and degree of covalent bonding are three determinative factors for the hardness of a polar covalent crystal. The low electronic density, greater bond length, and high ionicity of LnO bonds result in the lowest hardness of pseudobinary crystals composed of LnO bonds. The hardness of pseudobinary crystals composed of AlO bonds are all larger than the average hardness of LnMgAl<sub>11</sub>O<sub>19</sub>. Among the pseudobinary crystals composed of AlO bonds, the hardness of pseudobinary crystals composed of tetrahedral AlO bonds is greatest. Among the pseudobinary crystals composed of octahedral AlO bonds, the hardness of pseudobinary crystals composed of Al5O5 bonds is greatest due to the greatest bond density of Al5O5 bonds.

Increasing the coordination of atoms will affect three determinative factors for the hardness. The packing efficiency of crystal structures will increase due to the increase of coordination, so bond density can be increased. This is the advantageous aspect of enlarging the hardness. Al505 bond is this case. However, increasing the average anion-cation distance due to the increase of coordination can result in hardness reduction, and ionicity of chemical bonds will be enhanced due to the increase of coordination. Therefore, the hardness of pseudobinary crystals composed of LnO bonds is lowest although their coordination number is highest. The hardness of pseudobinary crystals composed of tetrahedral Al30 bonds is greatest owing to their lowest average coordination number.

#### 4. Conclusion

The chemical bond parameters of LnMgAl $_{11}O_{19}$  were calculated using the chemical bond dielectric theory of complex structural crystals. The hardness of LnMgAl $_{11}O_{19}$  was predicted. Results are in agreement with the experimental values. The calculations revealed that the origin of the high hardness of LnMgAl $_{11}O_{19}$  results mainly from AlO units.

#### References

- [1] K. Kahn, A.M. Lejus, M. Madsac, J. Thery, D. Vivien, J.C. Bernie, J. Appl. Phys. 52 (1981) 6864.
- [2] D. Saber, A.M. Lejus, Materials Research Bulletin 16 (1981) 1325–1330.
- [3] N.P. Bansal, D.M. Zhu, Surf. Coat. Technol. 202 (2008) 2698-2703.
- [4] S.Y. Zhang, Chin. J. Chem. Phys. 4 (1991) 109-115.
- [5] S.Y. Zhang, F.M. Gao, C.X. Wu, J. Alloys Compd. 275-277 (1998) 835-837.
- [6] J.C. Phillips, Rev. Mod. Phys. 42 (1970) 317.
- [7] F.M. Gao, S.Y. Zhang, Chinese Journal of Inorganic Chemistry 16 (2000) 751–756.
- [8] F.M. Gao, D.C. Li, S.Y. Zhang, Journal of Physics-Condensed Matter 15 (2003) 5079–5084.
- [9] F.M. Gao, Physical Review B 69 (2004) 094113.